

100-Pin TQFP
Industrial Temp

256K x 36
9Mb Sync Burst SRAM

250 MHz–200 MHz
1.8 V or 2.5 V V_{DD}
1.8 V or 2.5 V I/O

Features

- Single Cycle Deselect (SCD) operation
- 1.8 V or 2.5 V +10%/–10% core power supply
- 1.8 V or 2.5 V I/O supply
- $\overline{LBO}$ pin for Linear or Interleaved Burst mode
- Internal input resistors on mode pins allow floating mode pins
- Default to Interleaved Pipeline mode
- Byte Write ($\overline{BW}$) and/or Global Write ($\overline{GW}$) operation
- Internal self-timed write cycle
- Automatic power-down for portable applications
- JEDEC-standard 100-lead TQFP package
- RoHS-compliant 100-lead TQFP package available

Functional Description

Applications

The GS88037CT-xxxIV is a 9,437,184-bit (8,388,608-bit for x32 version) high performance synchronous SRAM with a 2-bit burst address counter. Although of a type originally developed for Level 2 Cache applications supporting high performance CPUs, the device now finds application in synchronous SRAM applications, ranging from DSP main store to networking chip set support.

Controls

Addresses, data I/Os, chip enables ($\overline{E1}$, $E2$, $\overline{E3}$), address burst control inputs ($\overline{ADSP}$, $\overline{ADSC}$, $\overline{ADV}$), and write control inputs ($\overline{Bx}$, $\overline{BW}$, $\overline{GW}$) are synchronous and are controlled by a positive-edge-triggered clock input (CK). Output enable ($\overline{G}$) and power down control (ZZ) are asynchronous inputs. Burst cycles can be initiated with either $\overline{ADSP}$ or $\overline{ADSC}$ inputs. In

Burst mode, subsequent burst addresses are generated internally and are controlled by $\overline{ADV}$. The burst address counter may be configured to count in either linear or interleave order with the Linear Burst Order ($\overline{LBO}$) input. The Burst function need not be used. New addresses can be loaded on every cycle with no degradation of chip performance.

SCD Pipelined Reads

The GS88037CT-xxxIV is a SCD (Single Cycle Deselect) pipelined synchronous SRAM. DCD (Dual Cycle Deselect) versions are also available. SCD SRAMs pipeline deselect commands one stage less than read commands. SCD RAMs begin turning off their outputs immediately after the deselect command has been captured in the input registers.

Byte Write and Global Write

Byte write operation is performed by using Byte Write enable ($\overline{BW}$) input combined with one or more individual byte write signals ($\overline{Bx}$). In addition, Global Write ($\overline{GW}$) is available for writing all bytes at one time, regardless of the Byte Write control inputs.

Sleep Mode

Low power (Sleep mode) is attained through the assertion (High) of the ZZ signal, or by stopping the clock (CK). Memory data is retained during Sleep mode.

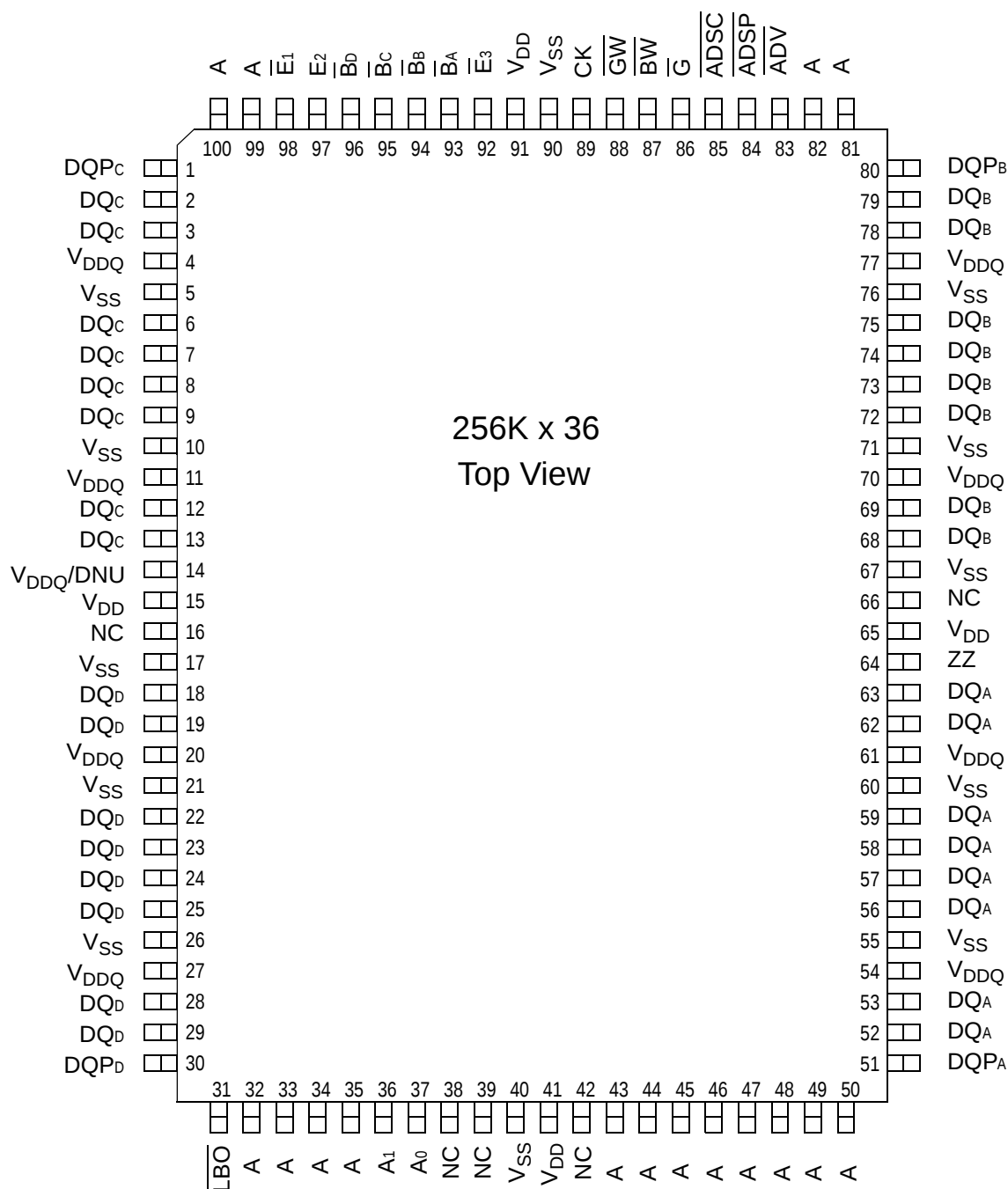
Core and Interface Voltages

The GS88037CT-xxxIV operates on a 1.8 V or 2.5 V power supply. All input are 2.5 V and 1.8 V compatible. Separate output power (V_{DDQ}) pins are used to decouple output noise from the internal circuits and are 2.5 V and 1.8 V compatible.

Parameter Synopsis

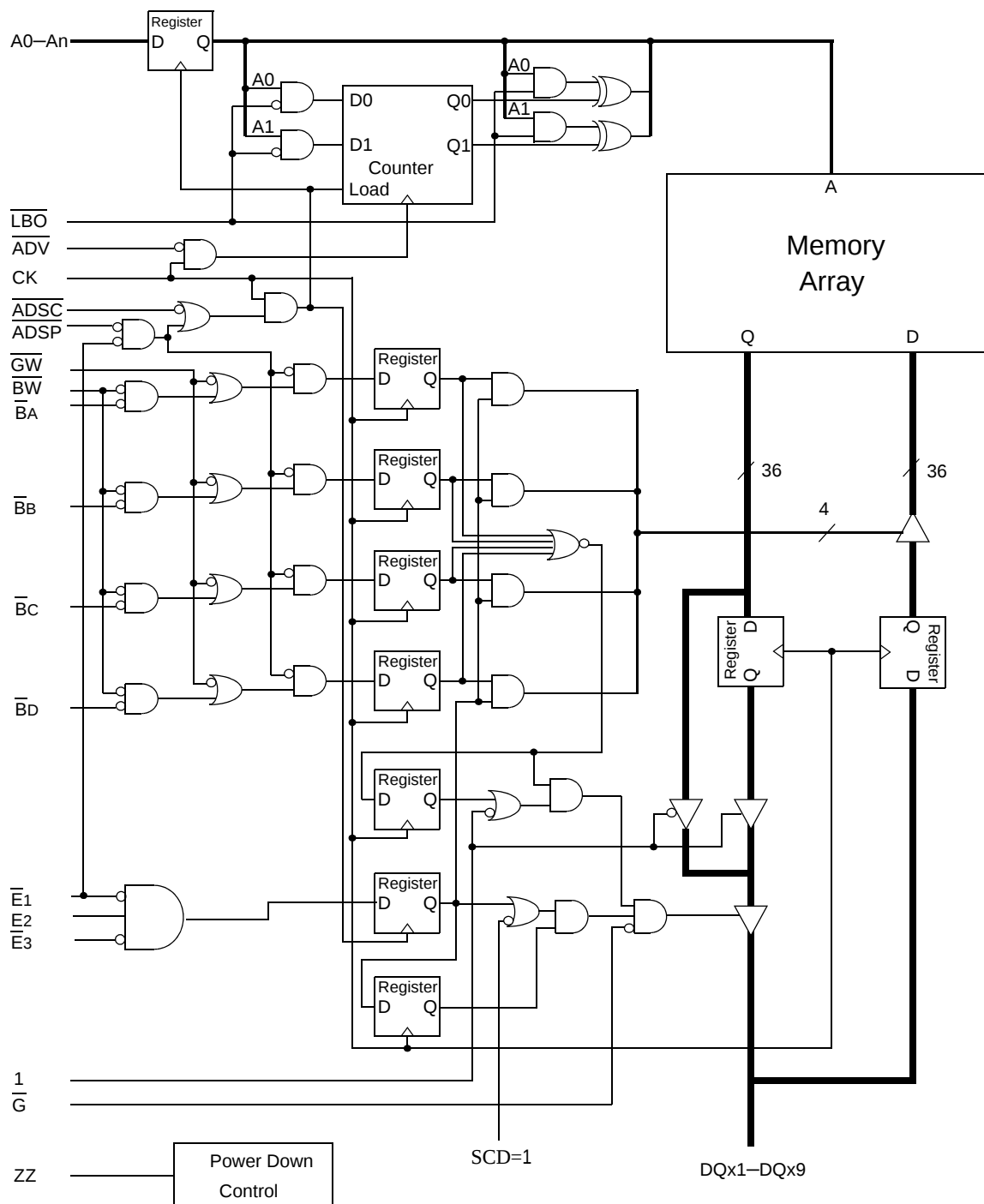
		-250I	-200I	Unit
Pipeline 3-1-1-1	t_{KQ}	2.3	2.7	ns
	t_{Cycle}	4.0	5.0	ns
	Curr (x36)	245	215	mA

GS88037CT-xxxIV 100-Pin TQFP Pinout


Note:

Pins marked with NC can be tied to either V_{DD} or V_{SS} . These pins can also be left floating.

GS88037CT-xxxIV Block Diagram



Note: Only x36 version shown for simplicity.

Byte Write Truth Table

Function	$\overline{GW}$	$\overline{BW}$	$\overline{BA}$	$\overline{BB}$	$\overline{BC}$	$\overline{BD}$	Notes
Read	H	H	X	X	X	X	1
Write No Bytes	H	L	H	H	H	H	1
Write byte a	H	L	L	H	H	H	2, 3
Write byte b	H	L	H	L	H	H	2, 3
Write byte c	H	L	H	H	L	H	2, 3, 4
Write byte d	H	L	H	H	H	L	2, 3, 4
Write all bytes	H	L	L	L	L	L	2, 3, 4
Write all bytes	L	X	X	X	X	X	

Notes:

1. All byte outputs are active in read cycles regardless of the state of Byte Write Enable inputs, $\overline{BA}$, $\overline{BB}$, $\overline{BC}$ and/or $\overline{BD}$.
2. Byte Write Enable inputs $\overline{BA}$, $\overline{BB}$, $\overline{BC}$ and/or $\overline{BD}$ may be used in any combination with $\overline{BW}$ to write single or multiple bytes.
3. All byte I/Os remain High-Z during all write operations regardless of the state of Byte Write Enable inputs.
4. Bytes "c" and "d" are only available on the x32 and x36 versions.

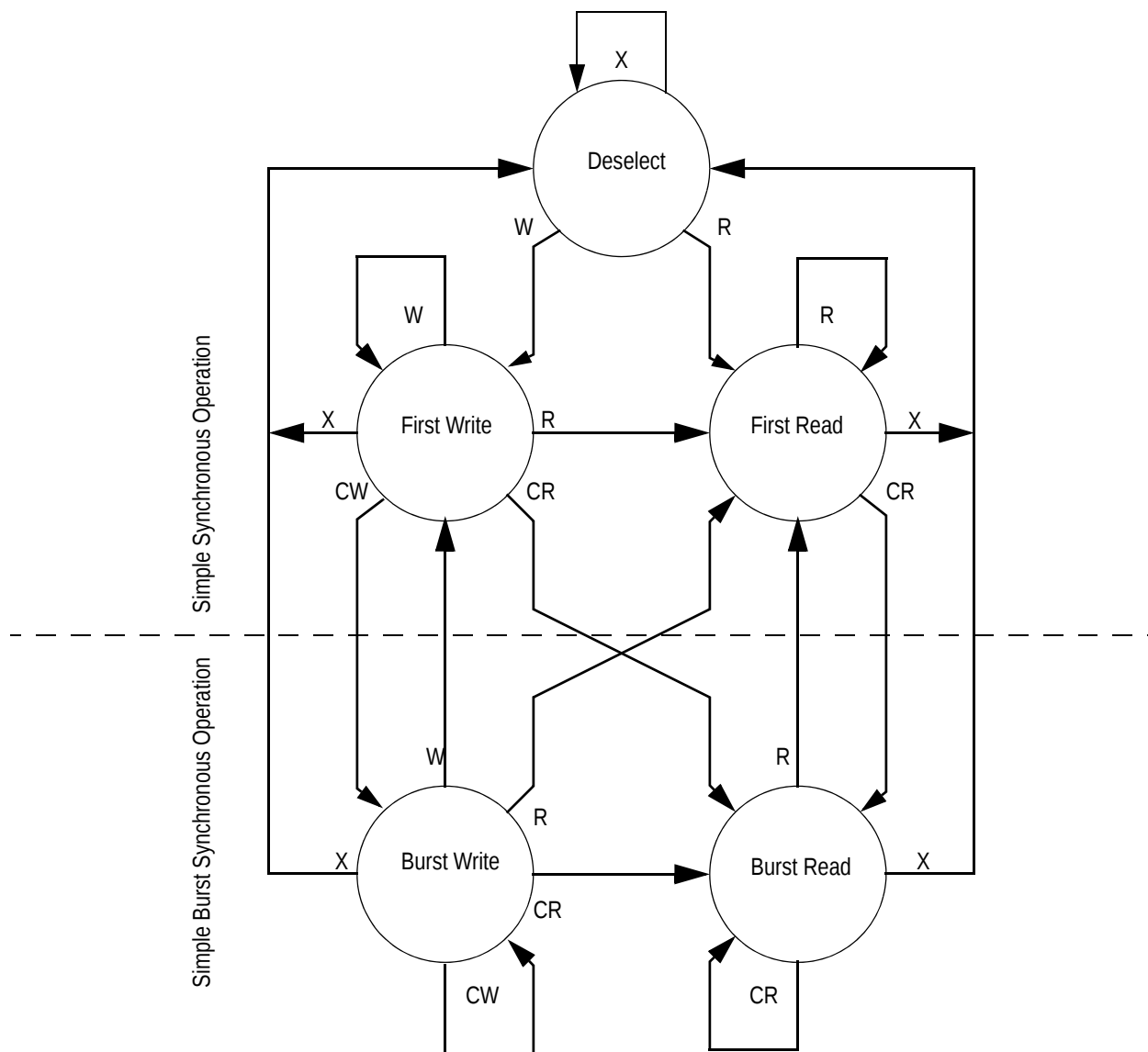
Synchronous Truth Table

Operation	Address Used	State Diagram Key	$\overline{E1}$	E2	$\overline{E3}$	$\overline{ADSP}$	$\overline{ADSC}$	$\overline{ADV}$	$\overline{W}$	DQ ³
Deselect Cycle, Power Down	None	X	L	X	H	X	L	X	X	High-Z
Deselect Cycle, Power Down	None	X	L	L	X	X	L	X	X	High-Z
Deselect Cycle, Power Down	None	X	L	X	H	L	X	X	X	High-Z
Deselect Cycle, Power Down	None	X	L	L	X	L	X	X	X	High-Z
Deselect Cycle, Power Down	None	X	H	X	X	X	L	X	X	High-Z
Read Cycle, Begin Burst	External	R	L	H	L	L	X	X	X	Q
Read Cycle, Begin Burst	External	R	L	H	L	H	L	X	F	Q
Write Cycle, Begin Burst	External	W	L	H	L	H	L	X	T	D
<i>Read Cycle, Continue Burst</i>	<i>Next</i>	<i>CR</i>	X	X	X	<i>H</i>	<i>H</i>	L	F	Q
Read Cycle, Continue Burst	Next	CR	H	X	X	X	H	L	F	Q
<i>Write Cycle, Continue Burst</i>	<i>Next</i>	<i>CW</i>	X	X	X	<i>H</i>	<i>H</i>	L	T	D
Write Cycle, Continue Burst	Next	CW	H	X	X	X	H	L	T	D
Read Cycle, Suspend Burst	Current		X	X	X	H	H	H	F	Q
Read Cycle, Suspend Burst	Current		H	X	X	X	H	H	F	Q
Write Cycle, Suspend Burst	Current		X	X	X	H	H	H	T	D
Write Cycle, Suspend Burst	Current		H	X	X	X	H	H	T	D

Notes:

1. X = Don't Care, H = High, L = Low
2. E = T (True) if E₂ = 1 and $\overline{E1} = \overline{E3} = 0$; E = F (False) if E₂ = 0 or $\overline{E1} = 1$ or $\overline{E3} = 1$
3. $\overline{W}$ = T (True) and F (False) is defined in the Byte Write Truth Table preceding.
4. $\overline{G}$ is an asynchronous input. $\overline{G}$ can be driven high at any time to disable active output drivers. $\overline{G}$ low can only enable active drivers (shown as "Q" in the Truth Table above).
5. All input combinations shown above are tested and supported. Input combinations shown in gray boxes need not be used to accomplish basic synchronous or synchronous burst operations and may be avoided for simplicity.
6. Tying $\overline{ADSP}$ high and $\overline{ADSC}$ low allows simple non-burst synchronous operations. See **BOLD** items above.
7. Tying $\overline{ADSP}$ high and $\overline{ADV}$ low while using $\overline{ADSC}$ to load new addresses allows simple burst operations. See *ITALIC* items above.

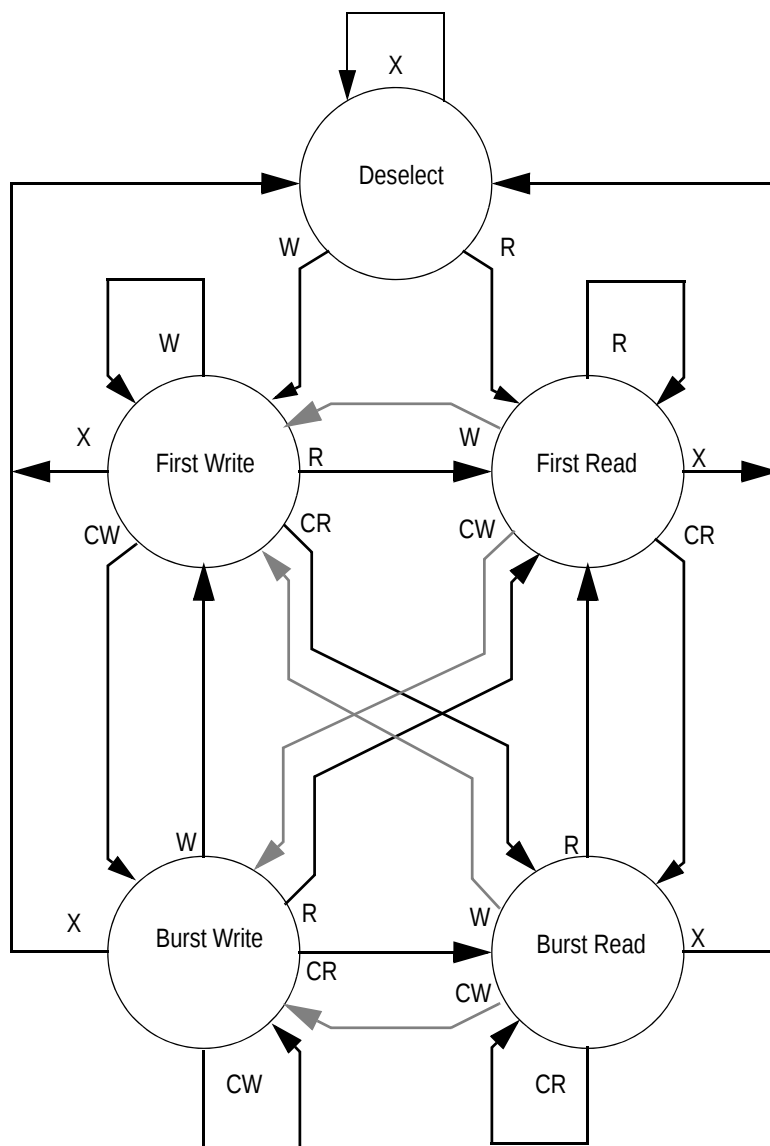
Simplified State Diagram



Notes:

1. The diagram shows only supported (tested) synchronous state transitions. The diagram presumes $\overline{G}$ is tied low.
2. The upper portion of the diagram assumes active use of only the Enable ($\overline{E1}$, $\overline{E2}$, and $\overline{E3}$) and Write ($\overline{BA}$, $\overline{BB}$, $\overline{BC}$, $\overline{BD}$, $\overline{BW}$, and $\overline{GW}$) control inputs, and that $\overline{ADSP}$ is tied high and $\overline{ADSC}$ is tied low.
3. The upper and lower portions of the diagram together assume active use of only the Enable, Write, and $\overline{ADSC}$ control inputs, and assumes $\overline{ADSP}$ is tied high and $\overline{ADV}$ is tied low.

Simplified State Diagram with $\overline{G}$



Notes:

1. The diagram shows supported (tested) synchronous state transitions plus supported transitions that depend upon the use of $\overline{G}$.
2. Use of "Dummy Reads" (Read Cycles with $\overline{G}$ High) may be used to make the transition from Read cycles to Write cycles without passing through a Deselect cycle. Dummy Read cycles increment the address counter just like normal read cycles.
3. Transitions shown in gray tone assume $\overline{G}$ has been pulsed high long enough to turn the RAM's drivers off and for incoming data to meet Data Input Set Up Time.

Absolute Maximum Ratings

(All voltages reference to V_{SS})

Symbol	Description	Value	Unit
V_{DD}	Voltage on V_{DD} Pins	−0.5 to 4.6	V
V_{DDQ}	Voltage on V_{DDQ} Pins	−0.5 to V_{DD}	V
$V_{I/O}$	Voltage on I/O Pins	−0.5 to $V_{DD} + 0.5$ (≤ 4.6 V max.)	V
V_{IN}	Voltage on Other Input Pins	−0.5 to $V_{DD} + 0.5$ (≤ 4.6 V max.)	V
I_{IN}	Input Current on Any Pin	+/−20	mA
I_{OUT}	Output Current on Any I/O Pin	+/−20	mA
P_D	Package Power Dissipation	1.5	W
T_{STG}	Storage Temperature	−55 to 125	°C
T_{BIAS}	Temperature Under Bias	−55 to 125	°C

Notes:

Permanent damage to the device may occur if the Absolute Maximum Ratings are exceeded. Operation should be restricted to Recommended Operating Conditions. Exposure to conditions exceeding the Absolute Maximum Ratings, for an extended period of time, may affect reliability of this component.

Power Supply Voltage Ranges

Parameter	Symbol	Min.	Typ.	Max.	Unit
1.8 V Supply Voltage	V_{DD1}	1.7	1.8	2.0	V
2.5 V Supply Voltage	V_{DD2}	2.3	2.5	2.7	V
1.8 V V_{DDQ} I/O Supply Voltage	V_{DDQ1}	1.7	1.8	2.0	V
2.5 V V_{DDQ} I/O Supply Voltage	V_{DDQ2}	2.3	2.5	2.7	V

Logic Levels

Parameter	Symbol	Min.	Typ.	Max.	Unit
V_{DD} Input High Voltage	V_{IH}	$0.6 \cdot V_{DD}$	—	$V_{DD} + 0.3$	V
V_{DD} Input Low Voltage	V_{IL}	−0.3	—	$0.3 \cdot V_{DD}$	V
V_{DDQ} Input High Voltage	V_{IHQ}	$0.6 \cdot V_{DD}$	—	$V_{DDQ} + 0.3$	V
V_{DDQ} Input Low Voltage	V_{ILQ}	−0.3	—	$0.3 \cdot V_{DD}$	V

Note:

V_{IHQ} (max) is voltage on V_{DDQ} pins plus 0.3 V.

Recommended Operating Temperatures

Parameter	Symbol	Min.	Typ.	Max.	Unit
Ambient Temperature (Industrial Range Versions)*	T_A	-40	25	85	°C

Note:

The part numbers of Industrial Temperature Range versions end with the character "I". Unless otherwise noted, all performance specifications quoted are evaluated for worst case in the temperature range marked on the device.

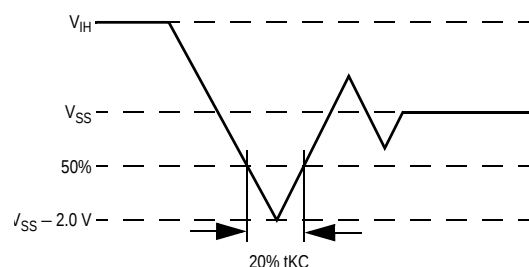
Thermal Impedance

Package	Test PCB Substrate	θ_{JA} (C°/W) Airflow = 0 m/s	θ_{JA} (C°/W) Airflow = 1 m/s	θ_{JA} (C°/W) Airflow = 2 m/s	θ_{JB} (C°/W)	θ_{JC} (C°/W)
100 TQFP	4-layer	38.7	33.5	31.9	27.6	10.6

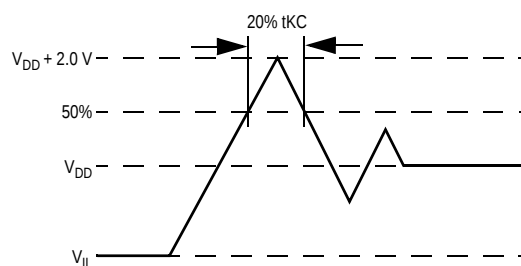
Notes:

1. Thermal Impedance data is based on a number of samples from multiple lots and should be viewed as a typical number.
2. Please refer to JEDEC standard JESD51-6.
3. The characteristics of the test fixture PCB influence reported thermal characteristics of the device. Be advised that a good thermal path to the PCB can result in cooling or heating of the RAM depending on PCB temperature.

Undershoot Measurement and Timing



Overshoot Measurement and Timing



Note:

Input Under/overshoot voltage must be $-2\text{ V} > V_i < V_{DDn} + 2\text{ V}$ not to exceed 4.6 V maximum, with a pulse width not to exceed $20\% \text{ tKC}$.

Capacitance

($T_A = 25^\circ\text{C}$, $f = 1\text{ MHz}$, $V_{DD} = 2.5\text{ V}$)

Parameter	Symbol	Test conditions	Typ.	Max.	Unit
Input Capacitance	C_{IN}	$V_{IN} = 0\text{ V}$	8	10	pF
Input/Output Capacitance	$C_{I/O}$	$V_{OUT} = 0\text{ V}$	12	14	pF

Note:

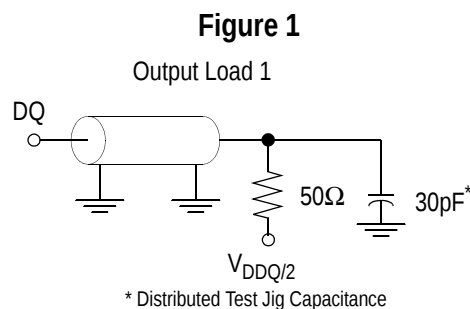
These parameters are sample tested.

AC Test Conditions

Parameter	Conditions
Input high level	$V_{DD} - 0.2\text{ V}$
Input low level	0.2 V
Input slew rate	1 V/ns
Input reference level	$V_{DD}/2$
Output reference level	$V_{DDQ}/2$
Output load	Fig. 1

Notes:

1. Include scope and jig capacitance.
2. Test conditions as specified with output loading as shown in **Fig. 1** unless otherwise noted.
3. Device is deselected as defined by the Truth Table.



DC Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Max
Input Leakage Current (except mode pins)	I_{IL}	$V_{IN} = 0\text{ to }V_{DD}$	$-1\text{ }\mu\text{A}$	$1\text{ }\mu\text{A}$
$\overline{\text{FT}}$ Input Current	I_{IN}	$V_{DD} \geq V_{IN} \geq 0\text{ V}$	$-100\text{ }\mu\text{A}$	$100\text{ }\mu\text{A}$
Output Leakage Current	I_{OL}	Output Disable, $V_{OUT} = 0\text{ to }V_{DD}$	$-1\text{ }\mu\text{A}$	$1\text{ }\mu\text{A}$
1.8 V Output High Voltage	V_{OH1}	$I_{OH} = -4\text{ mA}$, $V_{DDQ} = 1.7\text{ V}$	$V_{DDQ} - 0.4\text{ V}$	—
2.5 V Output High Voltage	V_{OH2}	$I_{OH} = -8\text{ mA}$, $V_{DDQ} = 2.375\text{ V}$	1.7 V	—
1.8 V Output Low Voltage	V_{OL1}	$I_{OL} = 4\text{ mA}$	—	0.4 V
2.5 V Output Low Voltage	V_{OL2}	$I_{OL} = 8\text{ mA}$	—	0.4 V

Operating Currents

Parameter	Test Conditions	Mode		Symbol	-250I	-200I	Unit
					-40 to 85°C	-40 to 85°C	
Operating Current	Device Selected; All other inputs $\geq V_{IH}$ or $\leq V_{IL}$ Output open	(x36)	Pipeline	I_{DD} I_{DDQ}	215 30	190 25	mA
Standby Current	$ZZ \geq V_{DD} - 0.2 V$	—	Pipeline	I_{SB}	45	45	mA
Deselect Current	Device Deselected; All other inputs $\geq V_{IH}$ or $\leq V_{IL}$	—	Pipeline	I_{DD}	85	85	mA

Notes:

- I_{DD} and I_{DDQ} apply to any combination of V_{DD1} , V_{DD2} , V_{DDQ1} , and V_{DDQ2} operation.
- All parameters listed are worst case scenario.

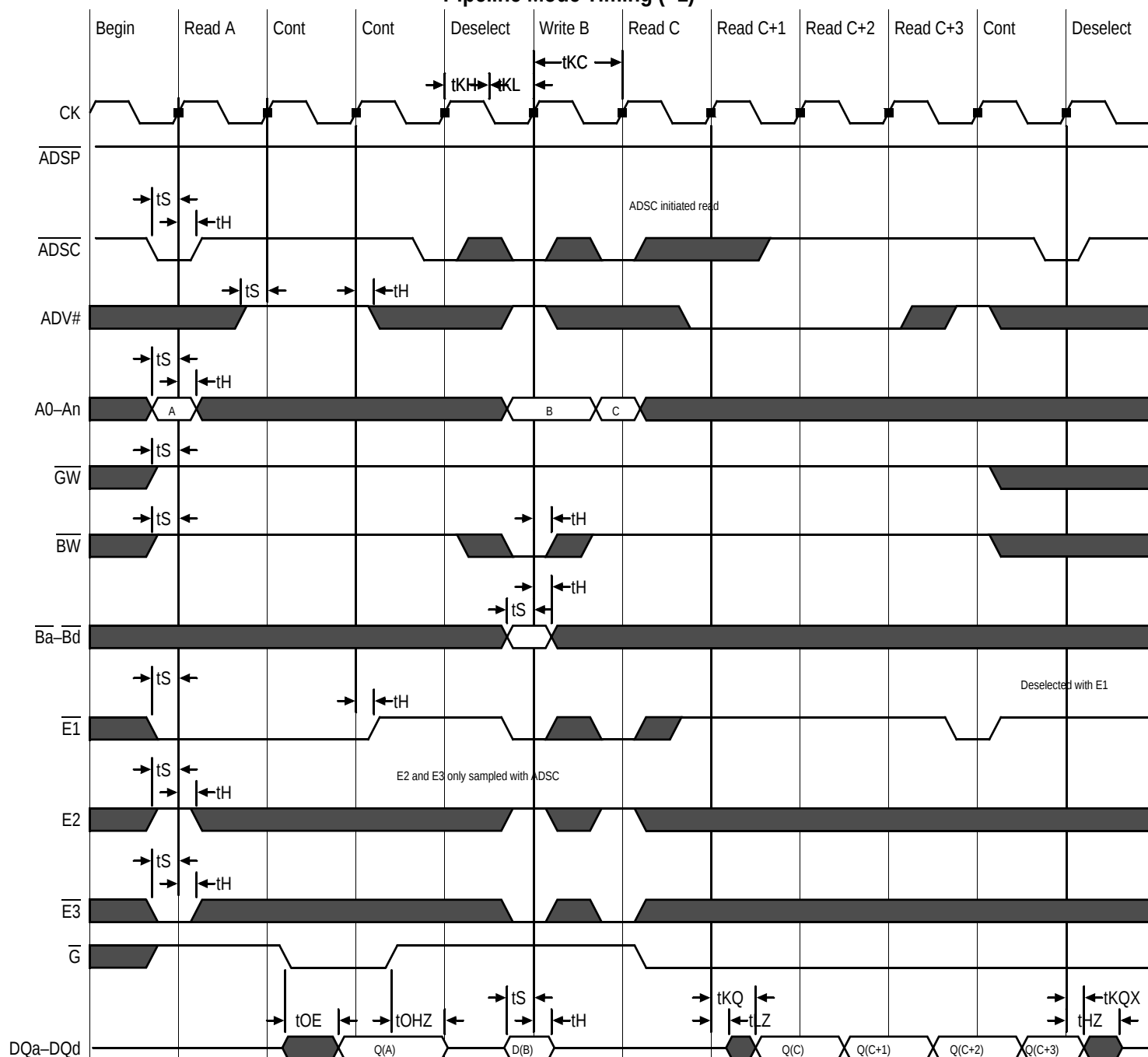
AC Electrical Characteristics

	Parameter	Symbol	-250I		-200I		Unit
			Min	Max	Min	Max	
Pipeline	Clock Cycle Time	t _{KC}	4.0	—	5.0	—	ns
	Clock to Output Valid	t _{KQ}	—	2.5	—	2.5	ns
	Clock to Output Invalid	t _{KQX}	1.0	—	1.0	—	ns
	Clock to Output in Low-Z	t _{LZ} ¹	1.0	—	1.0	—	ns
	Setup time	t _S	1.2	—	1.4	—	ns
	Hold time	t _H	0.2	—	0.4	—	ns
	$\bar{G}$ to Output Valid	t _{OE}	—	2.3	—	2.5	ns
	$\bar{G}$ to output in High-Z	t _{OHZ} ¹	—	2.3	—	2.5	ns
	Clock HIGH Time	t _{KH}	1.3	—	1.3	—	ns
	Clock LOW Time	t _{KL}	1.7	—	1.7	—	ns
	Clock to Output in High-Z	t _{HZ} ¹	1.0	2.3	1.0	2.5	ns
	$\bar{G}$ to output in Low-Z	t _{OLZ} ¹	0	—	0	—	ns
	ZZ setup time	t _{ZZS} ²	5	—	5	—	ns
	ZZ hold time	t _{ZZH} ²	1	—	1	—	ns
	ZZ recovery	t _{ZZR}	20	—	20	—	ns

Notes:

1. These parameters are sampled and are not 100% tested.
2. ZZ is an asynchronous signal. However, in order to be recognized on any given clock cycle, ZZ must meet the specified setup and hold times as specified above.

Pipeline Mode Timing (+1)

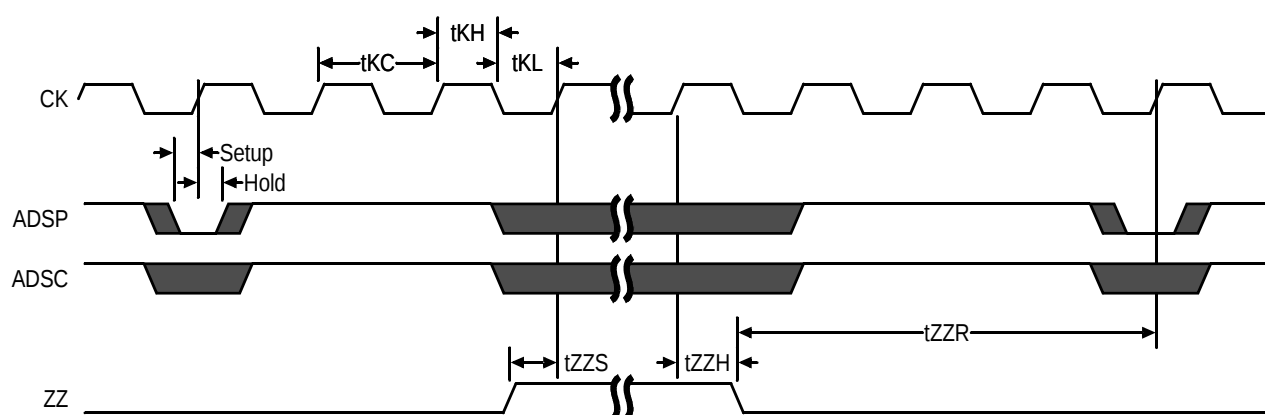


Sleep Mode

During normal operation, ZZ must be pulled low, either by the user or by its internal pull down resistor. When ZZ is pulled high, the SRAM will enter a Power Sleep mode after 2 cycles. At this time, internal state of the SRAM is preserved. When ZZ returns to low, the SRAM operates normally after ZZ recovery time.

Sleep mode is a low current, power-down mode in which the device is deselected and current is reduced to I_{SB2} . The duration of Sleep mode is dictated by the length of time the ZZ is in a High state. After entering Sleep mode, all inputs except ZZ become disabled and all outputs go to High-Z. The ZZ pin is an asynchronous, active high input that causes the device to enter Sleep mode. When the ZZ pin is driven high, I_{SB2} is guaranteed after the time t_{ZZI} is met. Because ZZ is an asynchronous input, pending operations or operations in progress may not be properly completed if ZZ is asserted. Therefore, Sleep mode must not be initiated until valid pending operations are completed. Similarly, when exiting Sleep mode during t_{ZZR} , only a Deselect or Read commands may be applied while the SRAM is recovering from Sleep mode.

Sleep Mode Timing Diagram



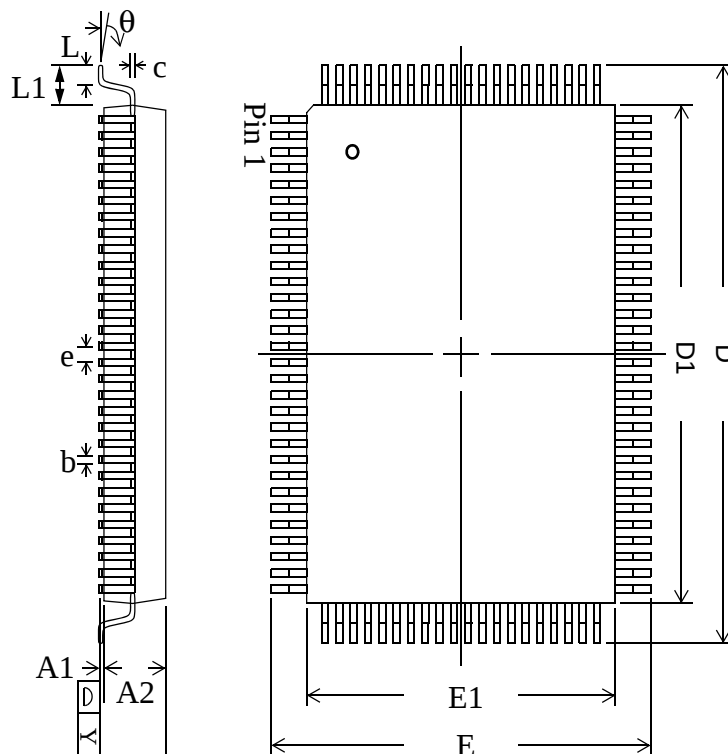
Application Tips

Single and Dual Cycle Deselect

SCD devices (like this one) force the use of “dummy read cycles” (read cycles that are launched normally but that are ended with the output drivers inactive) in a fully synchronous environment. Dummy read cycles waste performance but their use usually assures there will be no bus contention in transitions from reads to writes or between banks of RAMs. DCD SRAMs do not waste bandwidth on dummy cycles and are logically simpler to manage in a multiple bank application (wait states need not be inserted at bank address boundary crossings) but greater care must be exercised to avoid excessive bus contention.

TQFP Package Drawing (Package T)

Symbol	Description	Min.	Nom.	Max
A1	Standoff	0.05	0.10	0.15
A2	Body Thickness	1.35	1.40	1.45
b	Lead Width	0.20	0.30	0.40
c	Lead Thickness	0.09	—	0.20
D	Terminal Dimension	21.9	22.0	22.1
D1	Package Body	19.9	20.0	20.1
E	Terminal Dimension	15.9	16.0	16.1
E1	Package Body	13.9	14.0	14.1
e	Lead Pitch	—	0.65	—
L	Foot Length	0.45	0.60	0.75
L1	Lead Length	—	1.00	—
Y	Coplanarity			0.10
θ	Lead Angle	0°	—	7°



Notes:

1. All dimensions are in millimeters (mm).
2. Package width and length do not include mold protrusion.

Ordering Information for GSI Synchronous Burst RAMs

Org	Part Number ¹	Type	Voltage Option	Package	Speed (MHz)	T _A ²
256K x 36	GS88037CT-250IV	Pipeline	1.8 V or 2.5 V	TQFP	250	I
256K x 36	GS88037CT-200IV	Pipeline	1.8 V or 2.5 V	TQFP	200	I
256K x 36	GS88037CGT-250IV	Pipeline	1.8 V or 2.5 V	RoHS-compliant TQFP	250	I
256K x 36	GS88037CGT-200IV	Pipeline	1.8 V or 2.5 V	RoHS-compliant TQFP	200	I

Notes:

- Customers requiring delivery in Tape and Reel should add the character "T" to the end of the part number. Example: GS88037CT-200IT.
- T_A = I = Industrial Temperature Range.
- GSI offers other versions this type of device in many different configurations and with a variety of different features, only some of which are covered in this data sheet. See the GSI Technology web site (www.gsitechnology.com) for a complete listing of current offerings.

9Mb Sync SRAM Datasheet Revision History

File Name	Types of Changes Format or Content	Revision
880V37C_r1		• Creation of new datasheet
880V37C_r1_01	Content	• Update to MP datasheet
88037C_V_r1_02	Content	• Updated Absolute Maximum Ratings • Deleted conditional text
88037C_V_r1_03	Content	• Updated Absolute Maximum Ratings • Added thermal information
88037C_V_r1_04_Ind	Content	• Updated Absolute Maximum Ratings • Removed all Comm Temp references

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9